



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

YASUMOTO, Tamihide

#11/c
Amndt
Group Art Unit: 2813

Serial No.: 09/995,575

Examiner: KIEHN, E.

Filed: November 29, 2001

6/28/03
P.T.O. Confirmation No.: 1497

For: **SEMICONDUCTOR DEVICE MANUFACTURING METHOD USING METAL SILICIDE REACTION AFTER ION IMPLANTATION IN SILICON WIRING**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

June 12, 2003

Sir:

In response to the Office Action dated March 13, 2003, please amend the above-identified application as follows:

RECEIVED
JUN 13 2003
TECHNOLOGY CENTER 2800